

PATENT APPLICATION

Atty. Docket No.: 4591-170
Applicant: Jong-ho LEE and Nae-In LEE
Filing Date: February 2, 2001

Serial No. Not Yet Assigned

Group: Not Yet Assigned

INFORMATION DISCLOSURE CITATION
FORM PTO-1449 (Modified)

4#

10971 U.S. PTO
09/776059
02/02/01U.S. PATENT DOCUMENTS

<u>Exam</u> <u>Init</u>	<u>Ref</u>	<u>Document</u> <u>Number</u>	<u>Issue</u> <u>Date</u>	<u>Name</u>	<u>Class</u>	<u>Sub-</u> <u>Class</u>
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FOREIGN PATENT DOCUMENTS

	<u>Document</u> <u>Number</u>	<u>Publication</u> <u>Date</u>	<u>Country</u>	<u>Name</u>
<u>Doc</u> _____	EP 0851473A2	07/01/1998	EPO	Kizllyalll
<u>5</u> _____	WO 00/01008	01/06/2000	PCT	Lam Research Corp.

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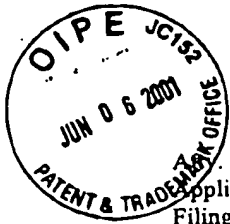
<u>Exam</u> <u>Init</u>	<u>Ref</u>	<u>(Including Author, Title, Date, Pertinent Pages, Etc.)</u>
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Examiner:

Roger Aille

Date Considered:

25 Mar 04



PATENT APPLICATION

Docket No.: 4591-170
Applicant: Jong-ho LEE, et al.
Filing Date: February 1, 2001

Serial No. 09/776,059
Group: 1773

INFORMATION DISCLOSURE CITATION
FORM PTO-1449 (Modified)U.S. PATENT DOCUMENTS

<u>Exam</u> <u>Init</u>	<u>Ref</u>	<u>Document</u> <u>Number</u>	<u>Issue</u> <u>Date</u>	<u>Name</u>	<u>Class</u>	<u>Sub-</u> <u>Class</u>
<u>DL</u>		5,923,056	07/13/99	Lee, et al.		
		6,013,553	01/11/00	Wallace, et al.		
		6,020,024	02/01/00	Maiti, et al.		
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<u>Document</u> <u>Number</u>	<u>Publication</u> <u>Date</u>	<u>Country</u>	<u>Name</u>

OTHER DOCUMENTS

<u>Exam</u> <u>Init</u>	<u>Ref</u>	<u>(Including Author, Title, Date, Pertinent Pages, etc.)</u>
		Wilk, G.D. and Wallace, R.M.; "Electrical Properties of hafnium silicate gate dielectrics deposited directly on silicon"; <u>Applied Physics Letters</u> ; pp 2854-2856 (1999)
		not provided

Examiner: Douglas Willo
Date Considered: 25 Mar 04